


## Brief CV

<b>Name</b>	ANIL ANNADI	中文名		
<b>Gender</b>	MALE	<b>Title</b> (Pro./Dr.)	Dr	
<b>Position</b> (President...)	RESEARCH FELLOW	<b>Country</b>	SINGAPORE	
<b>University/ Department</b>	National University of Singapore/ Department of Materials Science and Engineering			
<b>Personal Website</b>	<a href="https://scholar.google.com/citations?user=-KXM1P8AAAAJ&amp;hl=en">https://scholar.google.com/citations?user=-KXM1P8AAAAJ&amp;hl=en</a>			
<b>Research Area</b>	Oxide Electronics, Oxide Heterostructures and Interfaces, Transparent Semiconductors			

### Brief introduction of your research experience:

My research thrust is focused on designing novel oxide and inorganic materials for novel solid state electronics and energy applications. My research expertise includes fabrication of thin film and their interfaces using variety of physical vapor deposition techniques and their electro-static field effect characterizations. In particular, novel and versatile LaAlO<sub>3</sub>/SrTiO<sub>3</sub> based oxide interfaces that exhibit high mobility two-dimensional electron gas systems were explored extensively with respect to crystallography, lattice strain polar/non-polar nature. These systems were further investigated for nanoscale quantum phenomena to utilize in novel solid state device functionalities, such as quantum point contacts. My current research interests are designing novel transparent conductors, in particular p-type materials SnO, and CuI for applications as hole transport layers in energy conversion solar cells and as thin film transistors.

### Research Experience:

2016-2017 Postdoctoral Scholar at The University of Chicago, USA.

2014-2016 Postdoctoral Associate at University of Pittsburgh, USA.

PH.D in Physics from National University of Singapore, Singapore.

\*\*\*\*\*All the columns need to be filled in.